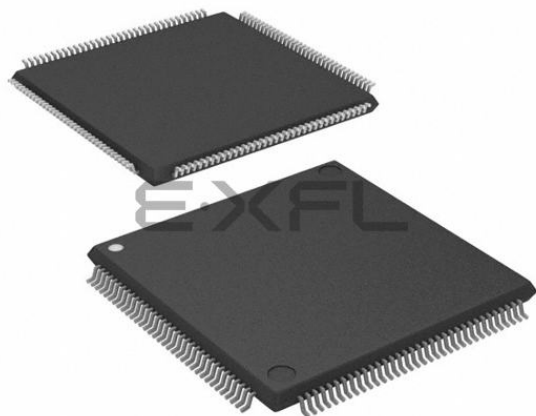




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[Embedded - System On Chip \(SoC\): The Heart of Modern Embedded Systems](#)

[Embedded - System On Chip \(SoC\)](#) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

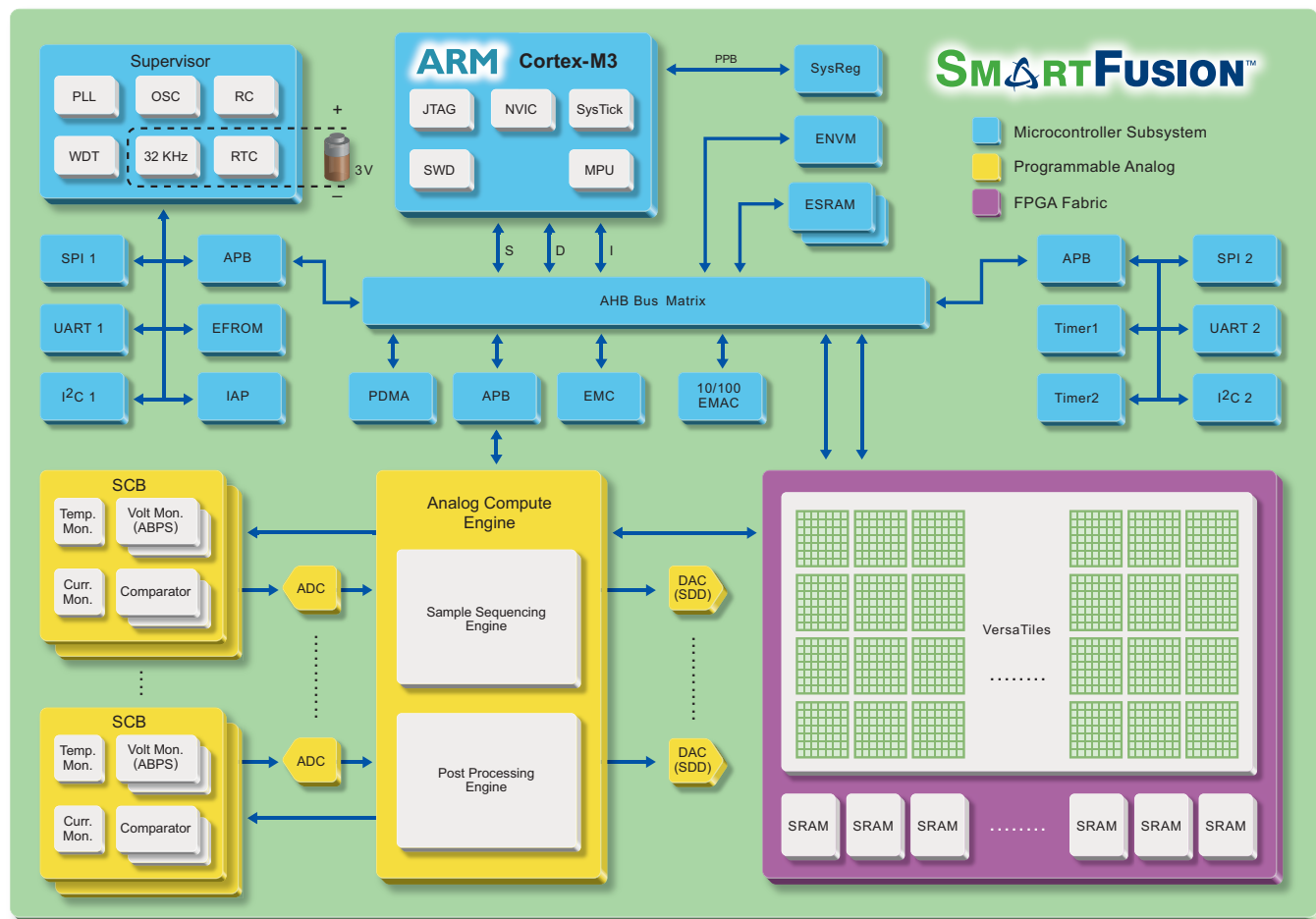
What are [Embedded - System On Chip \(SoC\)](#)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Obsolete
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	128KB
RAM Size	16KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, I ² C, SPI, UART/USART
Speed	80MHz
Primary Attributes	ProASIC®3 FPGA, 60K Gates, 1536D-Flip-Flops
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a2f060m3e-tqg144i

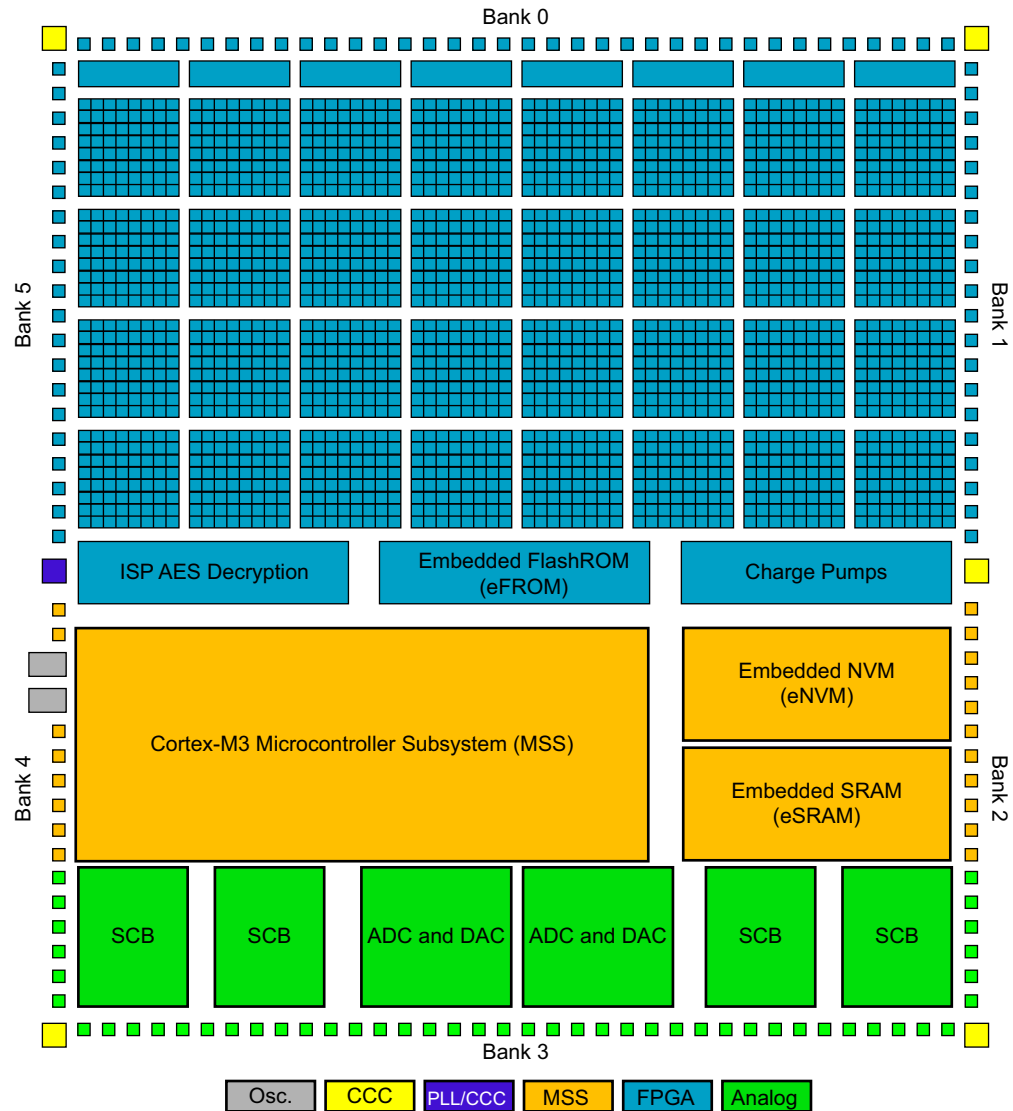
SmartFusion cSoC Block Diagram



Legend:

- SDD – Sigma-delta DAC
- SCB – Signal conditioning block
- PDMA – Peripheral DMA
- IAP – In-application programming
- ABPS – Active bipolar prescaler
- WDT – Watchdog Timer
- SWD – Serial Wire Debug

SmartFusion cSoC System Architecture



Note: Architecture for A2F200

Calculating Power Dissipation

Quiescent Supply Current

Table 2-8 • Power Supplies Configuration

Modes and Power Supplies	VCCxxxIOBx VCCFPGAIOBx VCCMSSIOBx	VCC33A / VCC33ADCx VCC33AP / VCC33SDDx VCCMAINXTAL / VCCLPXTAL	VCC / VCC15A / VCC15ADCx VCCPLLx, VCCENVM, VCCESRAM	VDDBAT	VCCRCOSC	VJTAG	VPP	eNVM (reset/off)	LPXTAL (enable/disable)	MAINXTAL (enable/disable)
Time Keeping mode	0 V	0 V	0 V	3.3 V	0 V	0 V	0 V	Off	Enable	Disable
Standby mode	On*	3.3 V	1.5 V	N/A	3.3 V	N/A	N/A	Reset	Enable	Disable
SoC mode	On*	3.3 V	1.5 V	N/A	3.3 V	N/A	N/A	On	Enable	Enable

Note: *On means proper voltage is applied. Refer to [Table 2-3 on page 2-3](#) for recommended operating conditions.

Table 2-9 • Quiescent Supply Current Characteristics

Parameter	Modes	A2F060		A2F200		A2F500	
		1.5 V Domain	3.3 V Domain	1.5 V Domain	3.3 V Domain	1.5 V Domain	3.3 V Domain
IDC1	SoC mode	3 mA	2 mA	7 mA	4 mA	16.5 mA	4 mA
IDC2	Standby mode	3 mA	2 mA	7 mA	4 mA	16.5 mA	4 mA
IDC3	Time Keeping mode	N/A	10 μ A	N/A	10 μ A	N/A	10 μ A

Power per I/O Pin

Table 2-10 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

	VCCFPGAIOBx (V)	Static Power PDC7 (mW)	Dynamic Power PAC9 (μ W/MHz)
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	–	17.55
2.5 V LVCMOS	2.5	–	5.97
1.8 V LVCMOS	1.8	–	2.88
1.5 V LVCMOS (JESD8-11)	1.5	–	2.33
3.3 V PCI	3.3	–	19.21
3.3 V PCI-X	3.3	–	19.21
Differential			
LVDS	2.5	2.26	0.82
LVPECL	3.3	5.72	1.16

Standby Mode

$$P_{\text{DYN}} = P_{\text{RC-OSC}} + P_{\text{LPXTAL-OSC}}$$

Time Keeping Mode

$$P_{\text{DYN}} = P_{\text{LPXTAL-OSC}}$$

Global Clock Dynamic Contribution— P_{CLOCK} **SoC Mode**

$$P_{\text{CLOCK}} = (P_{\text{AC1}} + N_{\text{SPINE}} * P_{\text{AC2}} + N_{\text{ROW}} * P_{\text{AC3}} + N_{\text{S-CELL}} * P_{\text{AC4}}) * F_{\text{CLK}}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Device Architecture" chapter of the [SmartFusion FPGA Fabric User's Guide](#).

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Device Architecture" chapter of the [SmartFusion FPGA Fabric User's Guide](#).

F_{CLK} is the global clock signal frequency.

$N_{\text{S-CELL}}$ is the number of VersaTiles used as sequential modules in the design.

Standby Mode and Time Keeping Mode

$$P_{\text{CLOCK}} = 0 \text{ W}$$

Sequential Cells Dynamic Contribution— $P_{\text{S-CELL}}$ **SoC Mode**

$$P_{\text{S-CELL}} = N_{\text{S-CELL}} * (P_{\text{AC5}} + (\alpha_1 / 2) * P_{\text{AC6}}) * F_{\text{CLK}}$$

$N_{\text{S-CELL}}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-17 on page 2-18](#).

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$$P_{\text{S-CELL}} = 0 \text{ W}$$

Combinatorial Cells Dynamic Contribution— $P_{\text{C-CELL}}$ **SoC Mode**

$$P_{\text{C-CELL}} = N_{\text{C-CELL}} * (\alpha_1 / 2) * P_{\text{AC7}} * F_{\text{CLK}}$$

$N_{\text{C-CELL}}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-17 on page 2-18](#).

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$$P_{\text{C-CELL}} = 0 \text{ W}$$

Routing Net Dynamic Contribution— P_{NET} **SoC Mode**

$$P_{\text{NET}} = (N_{\text{S-CELL}} + N_{\text{C-CELL}}) * (\alpha_1 / 2) * P_{\text{AC8}} * F_{\text{CLK}}$$

$N_{\text{S-CELL}}$ is the number VersaTiles used as sequential modules in the design.

$N_{\text{C-CELL}}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-17 on page 2-18](#).

F_{CLK} is the frequency of the clock driving the logic including these nets.

$$P_{PLL} = 0 \text{ W}$$

Embedded Nonvolatile Memory Dynamic Contribution— P_{eNVM}

SoC Mode

The eNVM dynamic power consumption is a piecewise linear function of frequency.

$$P_{eNVM} = N_{eNVM-BLOCKS} * \beta_4 * P_{AC15} * F_{READ-eNVM} \text{ when } F_{READ-eNVM} \leq 33 \text{ MHz,}$$

$$P_{eNVM} = N_{eNVM-BLOCKS} * \beta_4 * (P_{AC16} + P_{AC17} * F_{READ-eNVM}) \text{ when } F_{READ-eNVM} > 33 \text{ MHz}$$

Where:

$N_{eNVM-BLOCKS}$ is the number of eNVM blocks used in the design.

β_4 is the eNVM enable rate for read operations. Default is 0 (eNVM mainly in idle state).

$F_{READ-eNVM}$ is the eNVM read clock frequency.

Standby Mode and Time Keeping Mode

$$P_{eNVM} = 0 \text{ W}$$

Main Crystal Oscillator Dynamic Contribution— $P_{XTL-OSC}$

SoC Mode

$$P_{XTL-OSC} = P_{AC18}$$

Standby Mode

$$P_{XTL-OSC} = 0 \text{ W}$$

Time Keeping Mode

$$P_{XTL-OSC} = 0 \text{ W}$$

Low Power Oscillator Crystal Dynamic Contribution— $P_{LPXTAL-OSC}$

Operating, Standby, and Time Keeping Mode

$$P_{LPXTAL-OSC} = P_{AC21}$$

RC Oscillator Dynamic Contribution— P_{RC-OSC}

SoC Mode

$$P_{RC-OSC} = P_{AC19A} + P_{AC19B}$$

Standby Mode and Time Keeping Mode

$$P_{RC-OSC} = 0 \text{ W}$$

Analog System Dynamic Contribution— P_{AB}

SoC Mode

$$P_{AB} = P_{AC23} * N_{TM} + P_{AC24} * N_{CM} + P_{AC25} * N_{ABPS} + P_{AC26} * N_{SDD} + P_{AC27} * N_{COMP} + P_{ADC} * N_{ADC} + P_{VR}$$

Where:

N_{CM} is the number of current monitor blocks

N_{TM} is the number of temperature monitor blocks

N_{SDD} is the number of sigma-delta DAC blocks

N_{ABPS} is the number of ABPS blocks

N_{ADC} is the number of ADC blocks

N_{COMP} is the number of comparator blocks

$$P_{VR} = P_{AC28}$$

$$P_{ADC} = P_{AC20A} + P_{AC20B}$$



Table 2-24 • Summary of I/O Timing Characteristics—Software Default Settings

–1 Speed Grade, Worst Commercial-Case Conditions: $T_J = 85^{\circ}\text{C}$, Worst Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx (per standard)
Applicable to FPGA I/O Banks, Assigned to EMC I/O Pins

I/O Standard	Drive Strength	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	High	35	–	0.50	2.81	0.03	0.81	0.32	2.86	2.23	2.55	2.82	4.58	3.94	ns
2.5 V LVCMOS	12 mA	High	35	–	0.50	2.73	0.03	1.03	0.32	2.88	2.69	2.62	2.70	4.60	4.41	ns
1.8 V LVCMOS	12 mA	High	35	–	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns
1.5 V LVCMOS	12 mA	High	35	–	0.50	3.24	0.03	1.12	0.32	3.30	2.79	3.10	3.27	5.02	4.50	ns
3.3 V PCI	Per PCI spec	High	10	25 ¹	0.50	2.11	0.03	0.68	0.32	2.15	1.57	2.55	2.82	3.87	3.28	ns
3.3 V PCI-X	Per PCI-X spec	High	10	25 ¹	0.50	2.11	0.03	0.64	0.32	2.15	1.57	2.55	2.82	3.87	3.28	ns
LVDS	24 mA	High	–	–	0.50	1.53	0.03	1.55	–	–	–	–	–	–	–	ns
LVPECL	24 mA	High	–	–	0.50	1.46	0.03	1.46	–	–	–	–	–	–	–	ns

Notes:

- Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-10 on page 2-39](#) for connectivity. This resistor is not required during normal operation.
- For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings

–1 Speed Grade, Worst Commercial-Case Conditions: $T_J = 85^{\circ}\text{C}$, Worst Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx (per standard)
Applicable to MSS I/O Banks

I/O Standard	Drive Strength	Slew Rate	Capacitive Load (pF)	External Resistor	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{PVS} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	High	10	–	0.18	1.92	0.07	0.78	1.09	0.18	1.96	1.55	1.83	2.04	ns
2.5 V LVCMOS	8 mA	High	10	–	0.18	1.96	0.07	0.99	1.16	0.18	2.00	1.82	1.82	1.93	ns
1.8 V LVCMOS	4 mA	High	10	–	0.18	2.31	0.07	0.91	1.37	0.18	2.35	2.27	1.84	1.87	ns
1.5 V LVCMOS	2 mA	High	10	–	0.18	2.70	0.07	1.07	1.55	0.18	2.75	2.67	1.87	1.85	ns

Notes:

- Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-10 on page 2-39](#) for connectivity. This resistor is not required during normal operation.
- For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Timing Characteristics

Table 2-44 • 2.5 V LVCMOS High Slew

Worst Commercial-Case Conditions: $T_J = 85^\circ\text{C}$, Worst-Case VCC = 1.425 V,

Worst-Case VCCxxxxIOBx = 2.3 V

Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.55	8.10	0.04	1.23	0.39	7.37	8.10	2.54	2.17	9.43	10.15	ns
	–1	0.46	6.75	0.03	1.03	0.32	6.14	6.75	2.12	1.81	7.85	8.46	ns
8 mA	Std.	0.55	4.85	0.04	1.23	0.39	4.76	4.85	2.90	2.83	6.82	6.91	ns
	–1	0.46	4.04	0.03	1.03	0.32	3.97	4.04	2.42	2.36	5.68	5.76	ns
12 mA	Std.	0.60	3.28	0.04	1.23	0.39	3.46	3.23	3.15	3.24	5.52	5.29	ns
	–1	0.50	2.73	0.03	1.03	0.32	2.88	2.69	2.62	2.70	4.60	4.41	ns
16 mA	Std.	0.60	3.09	0.04	1.23	0.39	3.27	2.88	3.20	3.35	5.33	4.94	ns
	–1	0.50	2.57	0.03	1.03	0.32	2.72	2.40	2.67	2.79	4.44	4.12	ns
24 mA	Std.	0.60	2.95	0.04	1.23	0.39	3.01	2.31	3.27	3.76	5.07	4.37	ns
	–1	0.50	2.46	0.03	1.03	0.32	2.51	1.93	2.73	3.13	4.22	3.64	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Table 2-45 • 2.5 V LVCMOS Low Slew

Worst Commercial-Case Conditions: $T_J = 85^\circ\text{C}$, Worst-Case VCC = 1.425 V,

Worst-Case VCCxxxxIOBx = 2.3 V

Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.55	10.50	0.04	1.23	0.39	10.69	10.50	2.54	2.07	12.75	12.56	ns
	–1	0.46	8.75	0.03	1.03	0.32	8.91	8.75	2.12	1.73	10.62	10.47	ns
8 mA	Std.	0.55	7.61	0.04	1.23	0.39	7.46	7.19	2.81	2.66	9.52	9.25	ns
	–1	0.46	6.34	0.03	1.03	0.32	6.22	5.99	2.34	2.22	7.93	7.71	ns
12 mA	Std.	0.60	5.92	0.04	1.23	0.39	5.79	5.45	3.04	3.06	7.85	7.51	ns
	–1	0.50	4.93	0.03	1.03	0.32	4.83	4.54	2.53	2.55	6.54	6.26	ns
16 mA	Std.	0.60	5.53	0.04	1.23	0.39	5.40	5.09	3.09	3.16	7.46	7.14	ns
	–1	0.50	4.61	0.03	1.03	0.32	4.50	4.24	2.58	2.64	6.22	5.95	ns
24 mA	Std.	0.60	5.18	0.04	1.23	0.39	5.28	5.14	3.27	3.64	7.34	7.20	ns
	–1	0.50	4.32	0.03	1.03	0.32	4.40	4.29	2.72	3.03	6.11	6.00	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Table 2-46 • 2.5 V LVCMOS High Slew

Worst Commercial-Case Conditions: $T_J = 85^\circ\text{C}$, Worst-Case VCC = 1.425 V,

Worst-Case VCCxxxxIOBx = 3.0 V

Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
8 mA	Std.	0.22	2.35	0.09	1.18	1.39	0.22	2.40	2.18	2.19	2.32	ns
	–1	0.18	1.96	0.07	0.99	1.16	0.18	2.00	1.82	1.82	1.93	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Timing Characteristics

Table 2-50 • 1.8 V LVCMOS High Slew

Worst Commercial-Case Conditions: $T_J = 85^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,

Worst-Case $V_{CC} \times \text{IOBx} = 1.7\text{ V}$

Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.60	11.06	0.04	1.14	0.39	8.61	11.06	2.61	1.59	10.67	13.12	ns
	–1	0.50	9.22	0.03	0.95	0.32	7.17	9.22	2.18	1.33	8.89	10.93	ns
4 mA	Std.	0.60	6.46	0.04	1.14	0.39	5.53	6.46	3.04	2.66	7.59	8.51	ns
	–1	0.50	5.38	0.03	0.95	0.32	4.61	5.38	2.54	2.22	6.33	7.10	ns
6 mA	Std.	0.60	4.16	0.04	1.14	0.39	3.99	4.16	3.34	3.18	6.05	6.22	ns
	–1	0.50	3.47	0.03	0.95	0.32	3.32	3.47	2.78	2.65	5.04	5.18	ns
8 mA	Std.	0.60	3.69	0.04	1.14	0.39	3.76	3.67	3.40	3.31	5.81	5.73	ns
	–1	0.50	3.07	0.03	0.95	0.32	3.13	3.06	2.84	2.76	4.85	4.78	ns
12 mA	Std.	0.60	3.38	0.04	1.14	0.39	3.44	2.86	3.50	3.82	5.50	4.91	ns
	–1	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns
16 mA	Std.	0.60	3.38	0.04	1.14	0.39	3.44	2.86	3.50	3.82	5.50	4.91	ns
	–1	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Table 2-51 • 1.8 V LVCMOS Low Slew

Worst Commercial-Case Conditions: $T_J = 85^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,

Worst-Case $V_{CC} \times \text{IOBx} = 1.7\text{ V}$

Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.60	14.24	0.04	1.14	0.39	13.47	14.24	2.62	1.54	15.53	16.30	ns
	–1	0.50	11.87	0.03	0.95	0.32	11.23	11.87	2.18	1.28	12.94	13.59	ns
4 mA	Std.	0.60	9.74	0.04	1.14	0.39	9.92	9.62	3.05	2.57	11.98	11.68	ns
	–1	0.50	8.11	0.03	0.95	0.32	8.26	8.02	2.54	2.14	9.98	9.74	ns
6 mA	Std.	0.60	7.67	0.04	1.14	0.39	7.81	7.24	3.34	3.08	9.87	9.30	ns
	–1	0.50	6.39	0.03	0.95	0.32	6.51	6.03	2.79	2.56	8.23	7.75	ns
8 mA	Std.	0.60	7.15	0.04	1.14	0.39	7.29	6.75	3.41	3.21	9.34	8.80	ns
	–1	0.50	5.96	0.03	0.95	0.32	6.07	5.62	2.84	2.68	7.79	7.34	ns
12 mA	Std.	0.60	6.76	0.04	1.14	0.39	6.89	6.75	3.50	3.70	8.95	8.81	ns
	–1	0.50	5.64	0.03	0.95	0.32	5.74	5.62	2.92	3.08	7.46	7.34	ns
16 mA	Std.	0.60	6.76	0.04	1.14	0.39	6.89	6.75	3.50	3.70	8.95	8.81	ns
	–1	0.50	5.64	0.03	0.95	0.32	5.74	5.62	2.92	3.08	7.46	7.34	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.

Table 2-66 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCFPGAIOBx	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-67 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V _{REF} (typ.) (V)
1.64	1.94	Cross point	–

* Measuring point = V_{trip} . See [Table 2-22 on page 2-24](#) for a complete table of trip points.

Timing Characteristics

Table 2-68 • LVPECL

Worst Commercial-Case Conditions: $T_J = 85^{\circ}\text{C}$, Worst-Case VCC = 1.425 V,

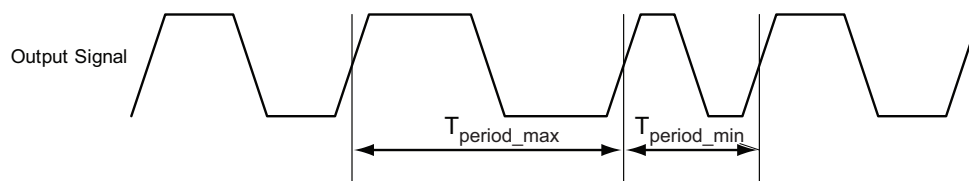
Worst-Case VCCFPGAIOBx = 3.0 V

Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.60	1.76	0.04	1.76	ns
–1	0.50	1.46	0.03	1.46	ns

Notes:

- For the derating values at specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-9](#) for derating values.
- The above mentioned timing parameters correspond to 24mA drive strength.



Note: Peak-to-peak jitter measurements are defined by $T_{\text{peak-to-peak}} = T_{\text{period_max}} - T_{\text{period_min}}$.

Figure 2-28 • Peak-to-Peak Jitter Definition

Table 2-88 • RAM512X18
Worst Commercial-Case Conditions: $T_J = 85^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.30	ns
t_{AH}	Address hold time	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.09	0.11	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	ns
t_{DS}	Input data (WD) setup time	0.19	0.22	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained, WMODE = 0)	2.19	2.63	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.91	1.09	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—applicable to opening edge	0.38	0.43	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—applicable to opening edge	0.44	0.50	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.94	1.12	ns
	RESET Low to data out Low on RD (pipelined)	0.94	1.12	ns
$t_{REMRSTB}$	RESET removal	0.29	0.35	ns
$t_{RECRSTB}$	RESET recovery	1.52	1.83	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.22	0.22	ns
t_{CYC}	Clock cycle time	3.28	3.28	ns
F_{MAX}	Maximum clock frequency	305	305	MHz

Notes:

1. For more information, refer to the [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#) application note.
2. For the derating values at specific junction temperature and voltage supply levels, refer to [Table 2-7](#) on [page 2-9](#) for derating values.

Programmable Analog Specifications

Current Monitor

Unless otherwise noted, current monitor performance is specified at 25°C with nominal power supply voltages, with the output measured using the internal voltage reference with the internal ADC in 12-bit mode and 91 Ksps, after digital compensation. All results are based on averaging over 16 samples.

Table 2-93 • Current Monitor Performance Specification

Specification	Test Conditions	Min.	Typical	Max.	Units
Input voltage range (for driving ADC over full range)		0 – 48	0 – 50	1 – 51	mV
Analog gain	From the differential voltage across the input pads to the ADC input		50		V/V
Input referred offset voltage	Input referred offset voltage	0	0.1	0.5	mV
	–40°C to +100°C	0	0.1	0.5	mV
Gain error	Slope of BFSL vs. 50 V/V		±0.1	±0.5	% nom.
	–40°C to +100°C			±0.5	% nom.
Overall Accuracy	Peak error from ideal transfer function, 25°C		±(0.1 + 0.25%)	±(0.4 + 1.5%)	mV plus % reading
Input referred noise	0 VDC input (no output averaging)	0.3	0.4	0.5	mVrms
Common-mode rejection ratio	0 V to 12 VDC common-mode voltage	–86	–87		dB
Analog settling time	To 0.1% of final value (with ADC load)				
	From CM_STB (High)	5			µs
	From ADC_START (High)	5		200	µs
Input capacitance			8		pF
Input biased current	CM[n] or TM[n] pad, –40°C to +100°C over maximum input voltage range (plus is into pad)				
	Strobe = 0; IBIAS on CM[n]		0		µA
	Strobe = 1; IBIAS on CM[n]		1		µA
	Strobe = 0; IBIAS on TM[n]		2		µA
	Strobe = 1; IBIAS on TM[n]		1		µA
Power supply rejection ratio	DC (0 – 10 KHz)	41	42		dB
Incremental operational current monitor power supply current requirements (per current monitor instance, not including ADC or VAREFx)	VCC33A		150		µA
	VCC33AP		140		µA
	VCC15A		50		µA

Note: Under no condition should the TM pad ever be greater than 10 mV above the CM pad. This restriction is applicable only if current monitor is used.

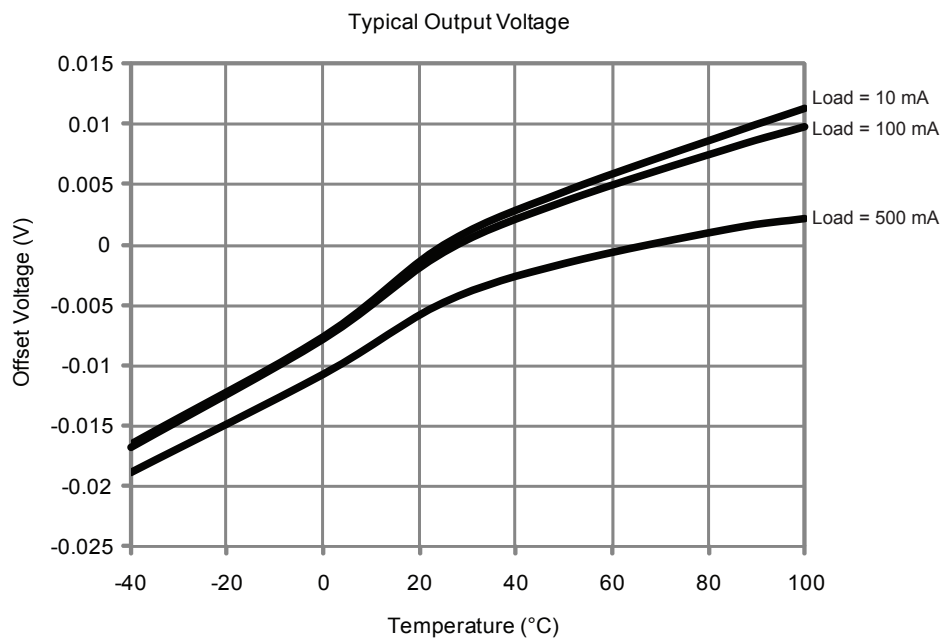


Figure 2-45 • Typical Output Voltage

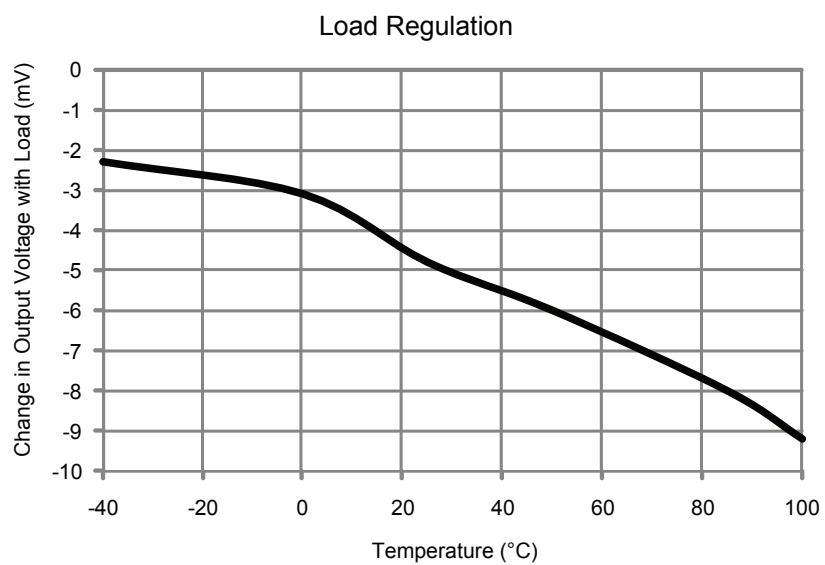


Figure 2-46 • Load Regulation

Inter-Integrated Circuit (I²C) Characteristics

This section describes the DC and switching of the I²C interface. Unless otherwise noted, all output characteristics given are for a 100 pF load on the pins. For timing parameter definitions, refer to [Figure 2-48 on page 2-92](#).

Table 2-101 • I²C Characteristics

Commercial Case Conditions: T_J = 85°C, V_{DD} = 1.425 V, –1 Speed Grade

Parameter	Definition	Condition	Value	Unit
V _{IL}	Minimum input low voltage	–	See Table 2-36 on page 2-30	–
	Maximum input low voltage	–	See Table 2-36	–
V _{IH}	Minimum input high voltage	–	See Table 2-36	–
	Maximum input high voltage	–	See Table 2-36	–
V _{OL}	Maximum output voltage low	I _{OL} = 8 mA	See Table 2-36	–
I _{IL}	Input current high	–	See Table 2-36	–
I _{IH}	Input current low	–	See Table 2-36	–
V _{hyst}	Hysteresis of Schmitt trigger inputs	–	See Table 2-33 on page 2-29	V
T _{FALL}	Fall time ²	VIHmin to VILMax, C _{load} = 400 pF	15.0	ns
		VIHmin to VILMax, C _{load} = 100 pF	4.0	ns
T _{RISE}	Rise time ²	VILMax to VIHmin, C _{load} = 400pF	19.5	ns
		VILMax to VIHmin, C _{load} = 100pF	5.2	ns
C _{in}	Pin capacitance	V _{IN} = 0, f = 1.0 MHz	8.0	pF
R _{pull-up}	Output buffer maximum pull-down Resistance ¹	–	50	Ω
R _{pull-down}	Output buffer maximum pull-up Resistance ¹	–	150	Ω
D _{max}	Maximum data rate	Fast mode	400	Kbps
t _{LOW}	Low period of I2C_x_SCL ³	–	1	clk cycles
t _{HIGH}	High period of I2C_x_SCL ³	–	1	clk cycles
t _{HD;STA}	START hold time ³	–	1	clk cycles
t _{SU;STA}	START setup time ³	–	1	clk cycles
t _{HD;DAT}	DATA hold time ³	–	1	clk cycles
t _{SU;DAT}	DATA setup time ³	–	1	clk cycles

Notes:

1. These maximum values are provided for information only. Minimum output buffer resistance values depend on VCCxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website at http://www.microsemi.com/index.php?option=com_microsemi&Itemid=489&lang=en&view=salescontact.
2. These values are provided for a load of 100 pF and 400 pF. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website at http://www.microsemi.com/index.php?option=com_microsemi&Itemid=489&lang=en&view=salescontact.
3. For allowable Pclk configurations, refer to the Inter-Integrated Circuit (I²C) Peripherals section in the [SmartFusion Microcontroller Subsystem User's Guide](#).

Re-Programming the eNVM Blocks Using the Cortex-M3

In this mode the Cortex-M3 is executing the eNVM programming algorithm from eSRAM. Since individual pages (132 bytes) of the eNVM can be write-protected, the programming algorithm software can be protected from inadvertent erasure. When reprogramming the eNVM, both MSS I/Os and FPGA I/Os are available as interfaces for sourcing the new eNVM image. The SoC Products Group provides working example projects for SoftConsole, IAR, and Keil development environments. These can be downloaded via the SoC Products Group Firmware Catalog.

Alternately, the eNVM can be reprogrammed by the Cortex-M3 via the IAP driver. This is necessary when using an encrypted image.

Secure Programming

For background, refer to the "Security in Low Power Flash Devices" chapter of the *Fusion FPGA Fabric User's Guide* on the SoC Products Group website. SmartFusion ISP behaves identically to Fusion ISP. IAP of SmartFusion cSoCs is accomplished by using the IAP driver. Only the FPGA fabric and the eNVM can be reprogrammed with the protection of security measures by using the IAP driver.

Typical Programming and Erase Times

Table 4-3 documents the typical programming and erase times for two components of SmartFusion cSoCs, FPGA fabric and eNVM, using the SoC Products Group's FlashPro hardware and software. These times will be different for other ISP and IAP methods. The **Program** action in FlashPro software includes erase, program, and verify to complete.

The typical programming (including erase) time per page of the eNVM is 8 ms.

Table 4-3 • Typical Programming and Erase Times

	FPGA Fabric (seconds)			eNVM (seconds)			FlashROM (seconds)		
	A2F060	A2F200	A2F500	A2F060	A2F200	A2F500	A2F060	A2F200	A2F500
Erase	21	21	21	N/A	N/A	N/A	21	21	21
Program	28	35	48	18	39	71	22	22	22
Verify	2	6	12	9	18	37	1	1	1

References

User's Guides

DirectC User's Guide

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=132588

In-System Programming (ISP) of Microsemi's Low-Power Flash Devices Using FlashPro4/3/3X

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129973

Programming Flash Devices HandBook

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129930

Application Notes on IAP Programming Technique

SmartFusion cSoC: Programming FPGA Fabric and eNVM Using In-Application Programming Interface App Note

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129818

SmartFusion cSoC: Basic Bootloader and Field Upgrade eNVM Through IAP Interface App Note

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129823

User-Defined Supply Pins

Name	Type	Polarity/ Bus Size	Description
VAREF0	Input	1	Analog reference voltage for first ADC. The SmartFusion cSoC can be configured to generate a 2.56 V internal reference that can be used by the ADC. While using the internal reference, the reference voltage is output on the VAREFOUT pin for use as a system reference. If a different reference voltage is required, it can be supplied by an external source and applied to this pin. The valid range of values that can be supplied to the ADC is 1.0 V to 3.3 V. When VAREF0 is internally generated, a bypass capacitor must be connected from this pin to ground. The value of the bypass capacitor should be between 3.3 μF and 22 μF, which is based on the needs of the individual designs. The choice of the capacitor value has an impact on the settling time it takes the VAREF0 signal to reach the required specification of 2.56 V to initiate valid conversions by the ADC. If the lower capacitor value is chosen, the settling time required for VAREF0 to achieve 2.56 V will be shorter than when selecting the larger capacitor value. The above range of capacitor values supports the accuracy specification of the ADC, which is detailed in the datasheet. Designers choosing the smaller capacitor value will not obtain as much margin in the accuracy as that achieved with a larger capacitor value. See the Analog-to-Digital Converter (ADC) section in the SmartFusion Programmable Analog User's Guide for more information. The SoC Products Group recommends customers use 10 μF as the value of the bypass capacitor. Designers choosing to use an external VAREF0 need to ensure that a stable and clean VAREF0 source is supplied to the VAREF0 pin before initiating conversions by the ADC. To use the internal voltage reference, the VAREFOUT pin must be connected to the appropriate ADC VAREF_x input on the PCB. For example, VAREFOUT can be connected to VAREF0 only, if ADC0 alone is used. VAREFOUT can be connected to VAREF1 only, if ADC1 alone is used. VAREFOUT can be connected to VAREF2 only, if ADC2 alone is used. VAREFOUT can be connected to VAREF0, VAREF1 and VAREF2 together, if ADC0, ADC1, and ADC2 all are used.
VAREF1	Input	1	Analog reference voltage for second ADC See "VAREF0" above for more information.
VAREF2	Input	1	Analog reference voltage for third ADC See "VAREF0" above for more.
VAREFOUT	Out	1	Internal 2.56 V voltage reference output. Can be used to provide the two ADCs with a unique voltage reference externally by connecting VAREFOUT to both VAREF0 and VAREF1. To use the internal voltage reference, you must connect the VAREFOUT pin to the appropriate ADC VAREF_x input—either the VAREF0 or VAREF1 pin—on the PCB.

Pin No.	CS288		
	A2F060 Function	A2F200 Function	A2F500 Function
K17	GNDLPXTAL	GNDLPXTAL	GNDLPXTAL
K19	GNDMAINXTAL	GNDMAINXTAL	GNDMAINXTAL
K21	MAINXIN	MAINXIN	MAINXIN
L1	GNDRCOSC	GNDRCOSC	GNDRCOSC
L3	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
L5	EMC_DB[2]/IO37NPB5V0	EMC_DB[2]/IO60NPB5V0	EMC_DB[2]/IO77NPB5V0
L6	NC	GNDQ	GNDQ
L8	VCC	VCC	VCC
L9	GND	GND	GND
L10	VCC	VCC	VCC
L12	VCC	VCC	VCC
L13	GND	GND	GND
L14	VCC	VCC	VCC
L16	VCCLPXTAL	VCCLPXTAL	VCCLPXTAL
L17	VDDBAT	VDDBAT	VDDBAT
L19	LPXIN	LPXIN	LPXIN
L21	MAINXOUT	MAINXOUT	MAINXOUT
M1	VCCRCOSC	VCCRCOSC	VCCRCOSC
M3	MSS_RESET_N	MSS_RESET_N	MSS_RESET_N
M5	GPIO_5/IO28RSB4V0	GPIO_5/IO42RSB4V0	GPIO_5/IO51RSB4V0
M6	GND	GND	GND
M8	GND	GND	GND
M9	VCC	VCC	VCC
M10	GND	GND	GND
M11	VCC	VCC	VCC
M12	GND	GND	GND
M13	VCC	VCC	VCC
M14	GND	GND	GND
M16	TMS	TMS	TMS
M17	VJTAG	VJTAG	VJTAG
M19	TDO	TDO	TDO

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.
2. *: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the [SmartFusion Microcontroller Subsystem User's Guide](#) for more details.

Pin Number	PQ208	
	A2F200	A2F500
1	VCCPLL	VCCPLL0
2	VCOMPLA	VCOMPLA0
3	GNDQ	GNDQ
4	EMC_DB[15]/GAA2/IO71PDB5V0	GAA2/IO88PDB5V0
5	EMC_DB[14]/GAB2/IO71NDB5V0	GAB2/IO88NDB5V0
6	EMC_DB[13]/GAC2/IO70PDB5V0	GAC2/IO87PDB5V0
7	EMC_DB[12]/IO70NDB5V0	IO87NDB5V0
8	VCC	VCC
9	GND	GND
10	VCCFPGAIOB5	VCCFPGAIOB5
11	EMC_DB[11]/IO69PDB5V0	IO86PDB5V0
12	EMC_DB[10]/IO69NDB5V0	IO86NDB5V0
13	GFA2/IO68PSB5V0	GFA2/IO85PSB5V0
14	GFA1/IO64PDB5V0	GFA1/IO81PDB5V0
15	GFA0/IO64NDB5V0	GFA0/IO81NDB5V0
16	EMC_DB[9]/GEC1/IO63PDB5V0	GEC1/IO80PDB5V0
17	EMC_DB[8]/GEC0/IO63NDB5V0	GEC0/IO80NDB5V0
18	EMC_DB[7]/GEB1/IO62PDB5V0	GEB1/IO79PDB5V0
19	EMC_DB[6]/GEB0/IO62NDB5V0	GEB0/IO79NDB5V0
20	EMC_DB[5]/GEA1/IO61PDB5V0	GEA1/IO78PDB5V0
21	EMC_DB[4]/GEA0/IO61NDB5V0	GEA0/IO78NDB5V0
22	VCC	VCC
23	GND	GND
24	VCCFPGAIOB5	VCCFPGAIOB5
25	EMC_DB[3]/GEC2/IO60PDB5V0	GEC2/IO77PDB5V0
26	EMC_DB[2]/IO60NDB5V0	IO77NDB5V0
27	EMC_DB[1]/GEB2/IO59PDB5V0	GEB2/IO76PDB5V0
28	EMC_DB[0]/GEA2/IO59NDB5V0	GEA2/IO76NDB5V0
29	VCC	VCC
30	GND	GND
31	GNDRCOSC	GNDRCOSC

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.
2. *: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the [SmartFusion Microcontroller Subsystem User's Guide](#) for more details.

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
H13	TDO	TDO	TDO
H14	TDI	TDI	TDI
H15	JTAGSEL	JTAGSEL	JTAGSEL
H16	GND	GND	GND
J1	EMC_DB[4]/IO38NPB5V0	EMC_DB[4]/GEA0/IO61NPB5V0	EMC_DB[4]/GEA0/IO78NPB5V0
J2	EMC_DB[3]/IO37PDB5V0	EMC_DB[3]/GEC2/IO60PDB5V0	EMC_DB[3]/GEC2/IO77PDB5V0
J3	EMC_DB[2]/IO37NDB5V0	EMC_DB[2]/IO60NDB5V0	EMC_DB[2]/IO77NDB5V0
J4	GNDRCOSC	GNDRCOSC	GNDRCOSC
J5	NC	GNDQ	GNDQ
J6	GND	GND	GND
J7	VCC	VCC	VCC
J8	GND	GND	GND
J9	VCC	VCC	VCC
J10	GND	GND	GND
J11	VCCMSSIOB2	VCCMSSIOB2	VCCMSSIOB2
J12	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23
J13	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22
J14	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31
J15	VCCMSSIOB2	VCCMSSIOB2	VCCMSSIOB2
J16	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30
K1	GPIO_1/IO32RSB4V0	MAC_MDIO/IO49RSB4V0	MAC_MDIO/IO58RSB4V0
K2	GPIO_0/IO33RSB4V0	MAC_MDC/IO48RSB4V0	MAC_MDC/IO57RSB4V0
K3	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4
K4	MSS_RESET_N	MSS_RESET_N	MSS_RESET_N
K5	VCCRCOSC	VCCRCOSC	VCCRCOSC
K6	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4
K7	GND	GND	GND
K8	VCC	VCC	VCC
K9	GND	GND	GND
K10	VCC	VCC	VCC
K11	GND	GND	GND

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.
2. *: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the [SmartFusion Microcontroller Subsystem User's Guide](#) for more details.